

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-8. (canceled)

9. (currently amended) A method of manufacturing a semiconductor device comprising steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

forming a first electrode comprising a laminate structure of a first conductive layer with a first width and a second conductive layer on said insulating film;

adding ~~[[an]]~~ first impurity ~~element~~ elements to said semiconductor layer using said first electrode as a mask to form a high concentration impurity region;

etching said second conductive layer to form a second electrode comprising a laminate structure of ~~[[the]]~~ said first conductive layer with said first width and said second conductive layer with a second width;

adding ~~[[the]]~~ second impurity ~~element~~ elements to said semiconductor layer using said second conductive layer as a mask to form a low concentration impurity region; and

after forming the low concentration impurity region, etching said first conductive layer to form a third electrode comprising a laminate structure of said first conductive layer with a third width and said second conductive layer with said second width.

10. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 9, wherein said second width is narrower than said first width.

11. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 9, wherein said third width is narrower than said first width and wider than said second width.

12. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 9, wherein said first impurity element is an elements and the second impurity elements are impurity ~~element~~ elements for imparting one of a n-type conductivity and a p-type conductivity to said semiconductor layer.

13. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 9, wherein a taper angle in an end portion of said ~~[[first]]~~ second conductive layer in said third electrode is larger than that in an end portion of said second conductive layer in said first electrode.

14. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 9, wherein a taper angle in an end portion of said first conductive layer in said third electrode is smaller than that in an end portion of said second conductive layer in said ~~[[second]]~~ third electrode.

15. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 9, wherein a taper angle of said first conductive layer in said third electrode is equal to that of said first conductive layer in said second electrode.

16. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 9, for forming said first electrode, comprising steps of:
laminating a first conductive film and a second conductive film on said insulating film;
a first etching process which is performed for said second conductive film; and

a second etching process which is performed for said first conductive film ~~to form said first electrode.~~

17. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 9, wherein said insulating film is removed to expose a portion of said high concentration impurity region simultaneously in forming said third electrode.

18. (currently amended) A method of manufacturing a semiconductor device comprising steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

forming a first electrode comprising a laminate structure of a first conductive layer with a first width and a second conductive layer on said insulating film;

etching said second conductive layer to form a second electrode comprising a laminate structure of said first conductive layer with said first width and said second conductive layer with a second width;

adding ~~[[an]]~~ first impurity element elements to said semiconductor layer using said second electrode as a mask to form a high concentration impurity region;

adding ~~[[said]]~~ second impurity element elements to said semiconductor layer ~~of the second electrode~~ through said first conductive layer of ~~[[the]]~~ said second electrode using ~~[[the]]~~ said second conductive layer of said second electrode as a mask to form a low concentration impurity region; and

etching said first conductive layer to form a third electrode comprising a laminate structure of said first conductive layer with a third width and said second conductive layer with said second width.

19. (currently amended) A method of manufacturing a semiconductor device comprising steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

forming a first electrode comprising a laminate structure of a first conductive layer with a first width and a second conductive layer on said insulating film;

etching said second conductive layer to form a second electrode comprising a laminate structure of said first conductive layer with said first width and said second conductive layer with a second width;

adding ~~[[an]]~~ impurity ~~element~~ elements to said semiconductor layer using said second conductive layer as a mask to form a low concentration impurity region and a high concentration impurity region; and

etching said first conductive layer to form a third electrode comprising a laminate structure of said first conductive layer with a third width and said second conductive layer with said second width.

20. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 18, wherein said second width is narrower than said first width.

21. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 19, wherein said second width is narrower than said first width.

22. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 18, wherein said third width is narrower than said first width and wider than said second width.

23. (currently amended) ~~A-manufacturing~~ The method of manufacturing the semiconductor device according to claim 19, wherein said third width is narrower than said first width and wider than said second width.

24. (currently amended) ~~A-manufacturing~~ The method of manufacturing the semiconductor device according to claim 18, wherein said first impurity element is an elements and said second impurity elements are impurity element elements for imparting one of a n-type conductivity and a p-type conductivity to said semiconductor layer.

25. (currently amended) ~~A-manufacturing~~ The method of manufacturing the semiconductor device according to claim 19, wherein said impurity ~~element is~~ elements are ~~[[an]]~~ impurity element elements for imparting one of a n-type conductivity and a p-type conductivity to said semiconductor layer.

26. (currently amended) ~~A-manufacturing~~ The method of manufacturing the semiconductor device according to claim 18, for forming said first electrode, comprising steps of:
laminating a first conductive film and a second conductive film on said insulating film;
a first etching process which is performed for said second conductive film; and
a second etching process which is performed for said first conductive film ~~to form said first electrode.~~

27. (currently amended) ~~A-manufacturing~~ The method of manufacturing the semiconductor device according to claim 19, for forming said first electrode, comprising steps of:
laminating a first conductive film and a second conductive film on said insulating film;
a first etching process which is performed for said second conductive film; and

a second etching process which is performed for said first conductive film ~~to form said first electrode.~~

28. (currently amended) A method of manufacturing a semiconductor device comprising steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

laminating a first conductive film and a second conductive film on said insulating film;

forming a second conductive layer with a first width by etching said second conductive film;

adding ~~[[an]]~~ first impurity ~~element~~ elements to said semiconductor layer using said second conductive layer with said first width as a mask to form a high concentration impurity region;

etching said first conductive film to form a first electrode comprising a laminate structure of a first conductive layer with a second width and said second conductive layer with a third width;

~~etching said second conductive layer to form a second electrode comprising a laminate structure of said first conductive layer with said second width and said second conductive layer with a fourth width;~~

adding ~~[[said]]~~ second impurity ~~element~~ elements to said semiconductor layer through said first conductive layer using said second conductive layer with said ~~[[fourth]]~~ third width as a mask to form a low concentration impurity region; and

etching said first conductive layer to form a ~~[[third]]~~ second electrode comprising a laminate structure of said first conductive layer with a ~~[[fifth]]~~ fourth width and said second conductive layer with said ~~[[fourth]]~~ third width.

29. (currently amended) ~~A-manufacturing~~ The method of manufacturing the semiconductor device according to claim 9, after the formation of said third electrode, further comprising steps of:

forming a first interlayer insulating film for covering said third electrode;

performing a first heat treatment for activating said first impurity element elements and said second impurity elements in said semiconductor layer;

forming a second interlayer insulating film for covering said first interlayer insulating film; and

performing a second heat treatment with a lower temperature than that in said first heat treatment after said second interlayer insulating film is formed.

30. (currently amended) ~~A-manufacturing~~ The method of manufacturing the semiconductor device according to claim 18, after the formation of said third electrode, further comprising steps of:

forming a first interlayer insulating film for covering said third electrode;

performing a first heat treatment for activating said first impurity element elements and said second impurity elements in said semiconductor layer;

forming a second interlayer insulating film for covering said first interlayer insulating film; and

performing a second heat treatment with a lower temperature than that in said first heat treatment after said second interlayer insulating film is formed.

31. (currently amended) ~~A-manufacturing~~ The method of manufacturing the semiconductor device according to claim 19, after the formation of said third electrode, further comprising steps of:

forming a first interlayer insulating film for covering said third electrode;

performing a first heat treatment for activating said impurity element elements in said semiconductor layer;

forming a second interlayer insulating film for covering said first interlayer insulating film; and

performing a second heat treatment with a lower temperature than that in said first heat treatment after said second interlayer insulating film is formed.

32. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 28, after the formation of said ~~[[third]]~~ second electrode, further comprising steps of:

forming a first interlayer insulating film for covering said ~~[[third]]~~ second electrode;

performing a first heat treatment for activating said first impurity ~~element~~ elements and said second impurity elements in said semiconductor layer;

forming a second interlayer insulating film for covering said first interlayer insulating film; and

performing a second heat treatment with a lower temperature than that in said first heat treatment after said second interlayer insulating film is formed.

33. (currently amended) A method of manufacturing a semiconductor device comprising steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

laminating a first conductive film and a second conductive film on said insulating film;

forming a second conductive layer with a first width by etching said second conductive film;

adding ~~[[an]]~~ first impurity ~~element~~ elements to said semiconductor layer using said second conductive layer with said first width as a mask to form a high concentration impurity region;

etching said second conductive layer to form said second conductive layer with a second width;

adding ~~[[an]]~~ second impurity ~~element~~ elements to said semiconductor layer through said first conductive film using said second conductive layer with said second width as a mask to form a low concentration impurity region; and

etching said first conductive film to form an electrode comprising a laminate structure of a first conductive layer with a third width and said second conductive layer with said second width.

34. (currently amended) ~~A manufacturing~~ The method of manufacturing the semiconductor device according to claim 33, after the formation of said third electrode, further comprising steps of:

forming a first interlayer insulating film for covering said third electrode;

performing a first heat treatment for activating said first impurity ~~element~~ elements and said second impurity elements in said semiconductor layer;

forming a second interlayer insulating film for covering said first interlayer insulating film; and

performing a second heat treatment with a lower temperature than that in said first heat treatment.

35. (currently amended) ~~A manufacturing~~ The method of [[a]] manufacturing the semiconductor device according to claim 9, wherein said semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, a portable information terminal, a digital video disk player, and an electronic game device.

36. (currently amended) ~~A manufacturing~~ The method of [[a]] manufacturing the semiconductor device according to claim 18, wherein said semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display,

a car navigation system, a personal computer, a portable information terminal, a digital video disk player, and an electronic game device.

37. (currently amended) ~~A-manufacturing~~ The method of [[a]] manufacturing the semiconductor device according to claim 19, wherein said semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, a portable information terminal, a digital video disk player, and an electronic game device.

38. (currently amended) ~~A-manufacturing~~ The method of [[a]] manufacturing the semiconductor device according to claim 28, wherein said semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, a portable information terminal, a digital video disk player, and an electronic game device.

39. (currently amended) ~~A-manufacturing~~ The method of [[a]] manufacturing the semiconductor device according to claim 33, wherein said semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, a portable information terminal, a digital video disk player, and an electronic game device.